

General Description

The WST02N30 is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

Features

- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

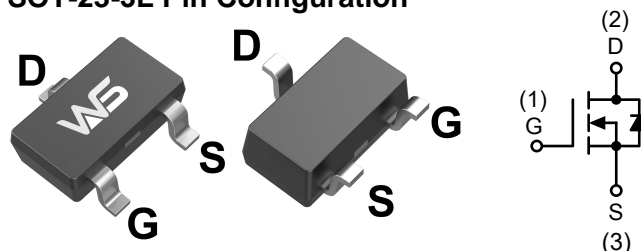
Product Summary

BV_{DSS}	$R_{DS(on)}$	I_D
300V	3000mΩ	2.0A

Applications

- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	300	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.0	A
$I_D@T_c=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.1	A
I_{DM}	Pulsed Drain Current ²	12	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	60	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	300	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.067	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=1.5A$	---	3000	4000	m Ω
		$V_{GS}=6V$, $I_D=0.5A$	---	4500	5500	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.0	3.0	4.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.2	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=300V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=240V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	100	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
Q_g	Total Gate Charge (10V)	$V_{DS}=240V$, $V_{GS}=10V$, $I_D=1A$	---	4.4	---	nC
Q_{gs}	Gate-Source Charge		---	0.7	---	
Q_{gd}	Gate-Drain Charge		---	2.0	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=150V$, $V_{GS}=10V$, $R_G=25\Omega$, $I_D=1A$.	---	18	---	ns
T_r	Rise Time		---	55	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	60	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	138	---	pF
C_{oss}	Output Capacitance		---	30	---	
C_{rss}	Reverse Transfer Capacitance		---	5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	2.0	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	12	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.4	V
t_{rr}	Reverse Recovery Time	$IF=1A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	250	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.8	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t<10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

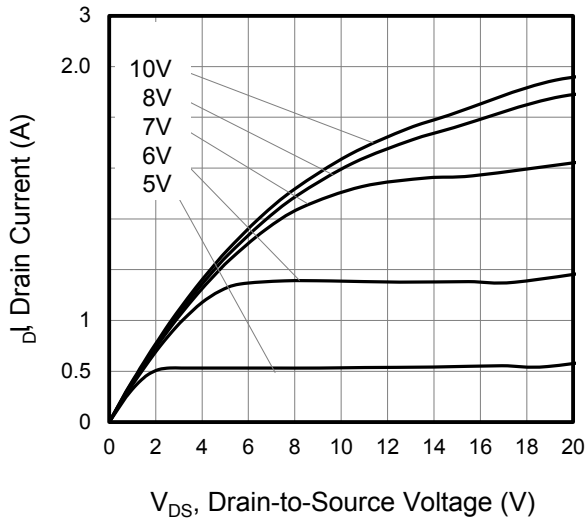
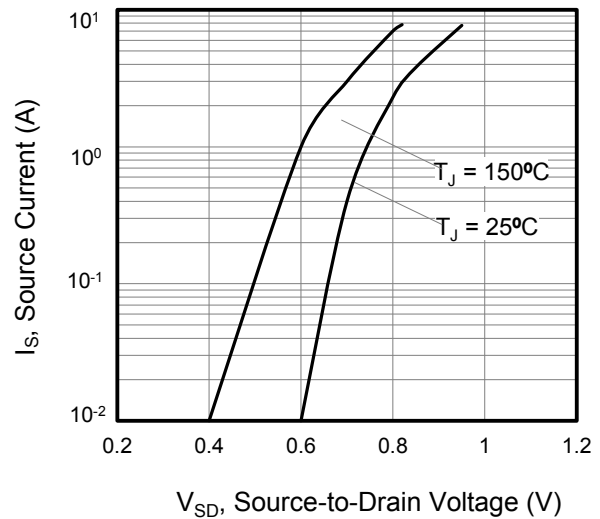
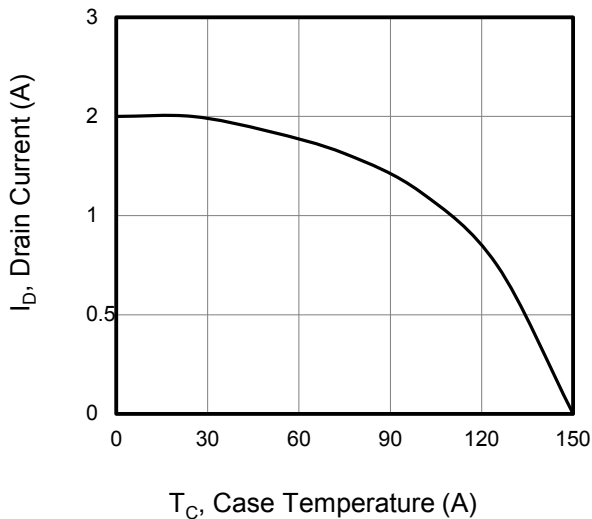
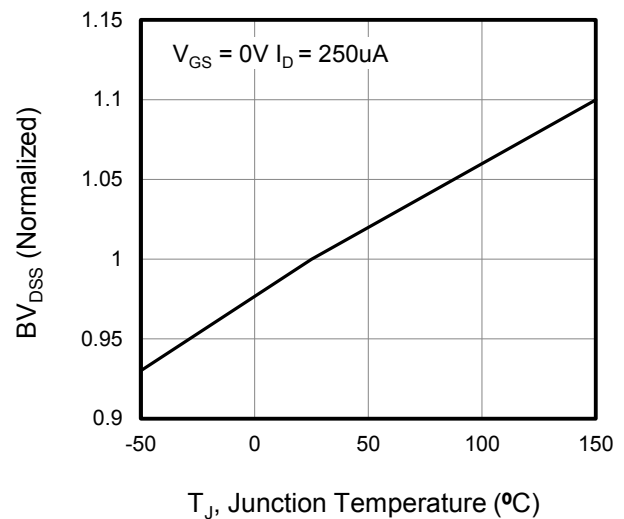
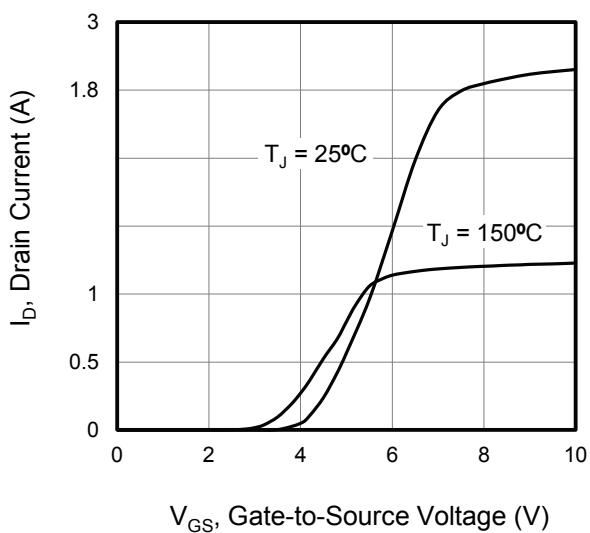
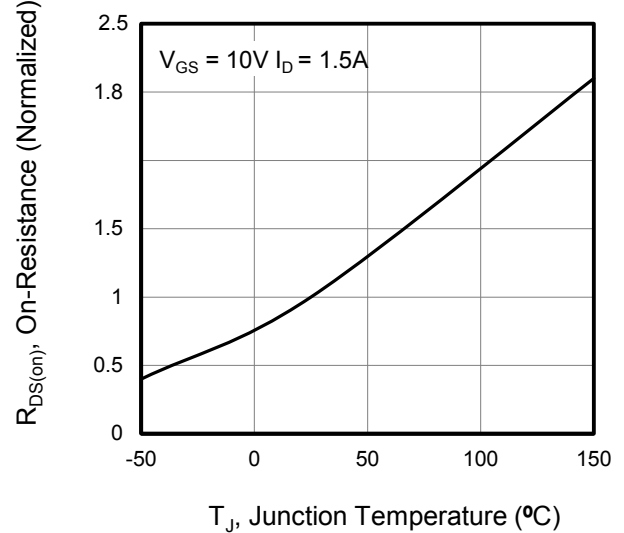
Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Body Diode Forward Voltage

Figure 3. Drain Current vs. Temperature

Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Transfer Characteristics

Figure 6. On-Resistance vs. Temperature


Figure 7. Capacitance

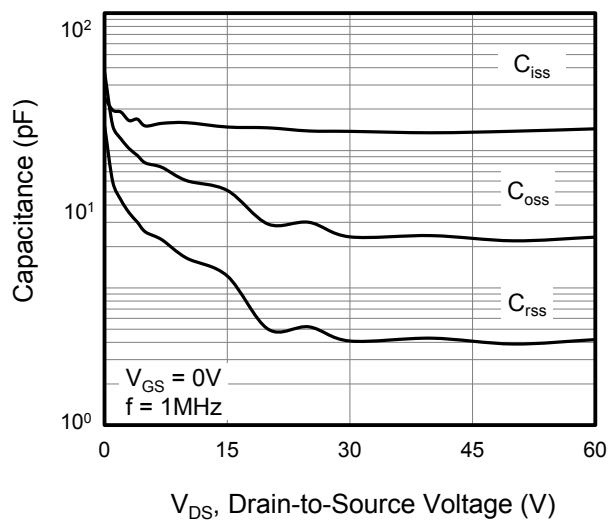


Figure 8. Gate Charge

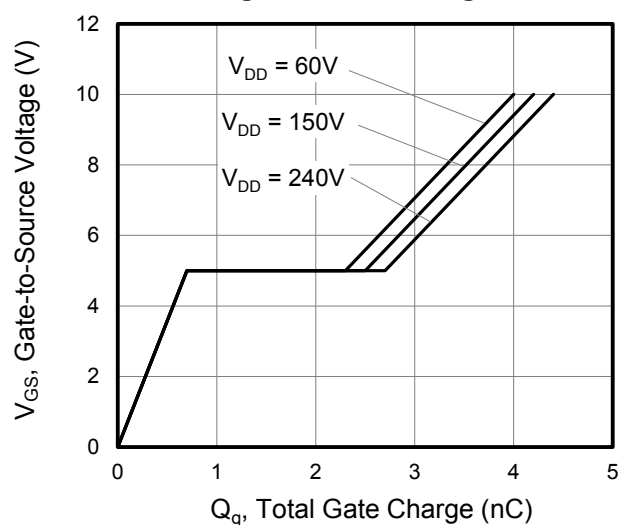
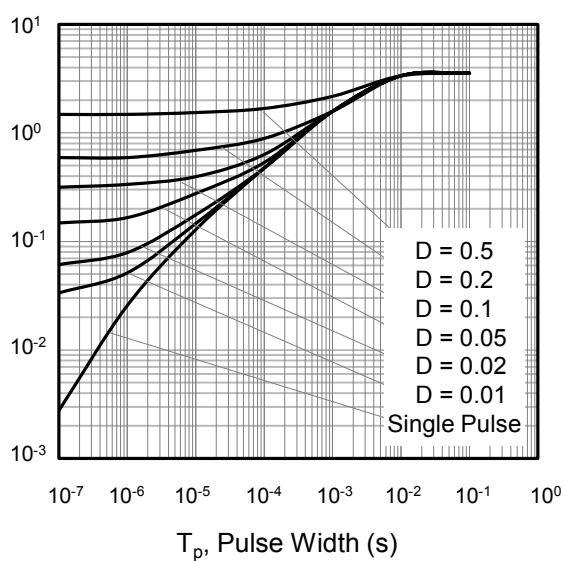
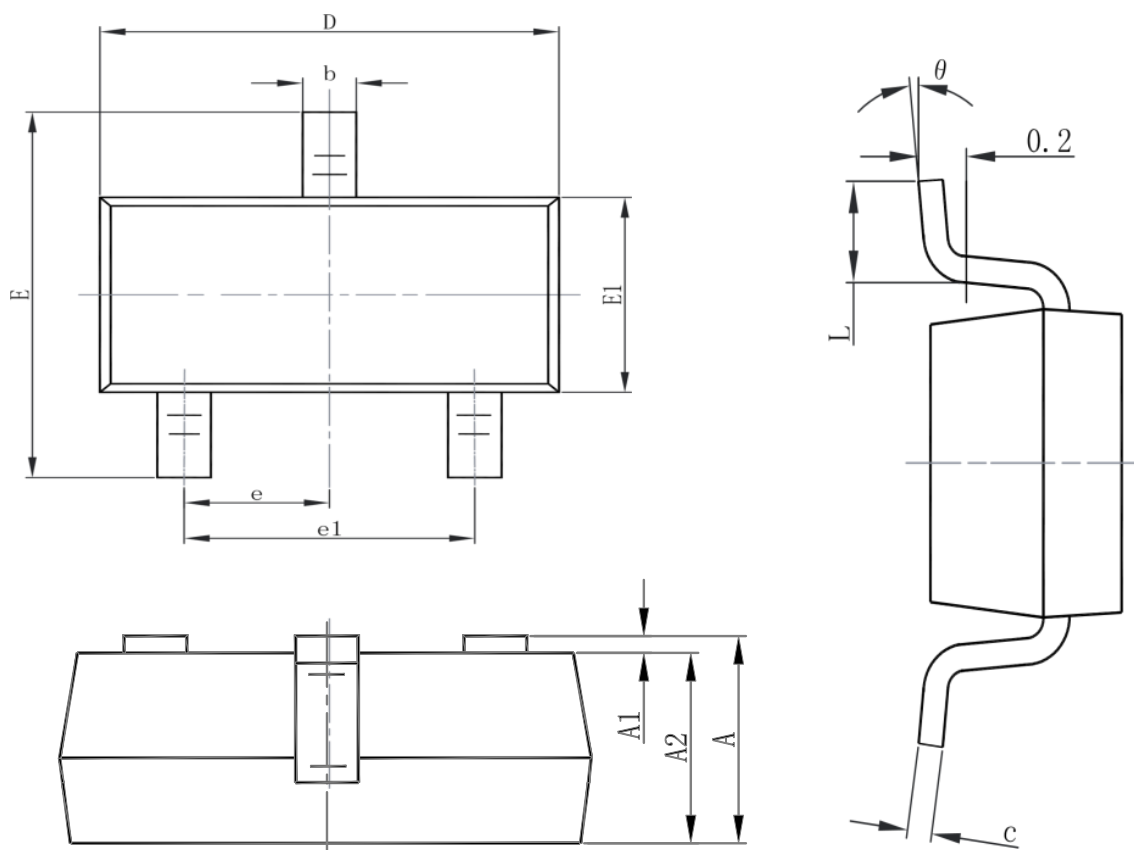


Figure 9. Transient Thermal Impedance



Packaging information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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